

IN THE CLAIMS

Please amend claims 29, 30, and 33 as follows:

Claims 1 -28. (Canceled)

1 29. (Currently Amended) A flat panel display, comprising a plurality of sub-pixels
2 driven by thin film transistors, each of the thin film transistors including a source electrode,
3 a drain electrode, a gate electrode, and a polysilicon semiconductor layer and each of the
4 sub-pixels including a first electrode, a second electrode, and an emitting layer disposed
5 between the first electrode and the second electrode, wherein one of the source electrode and
6 the drain electrode includes:

7 a first titanium layer contacting the semiconductor layer;
8 an aluminum-based metal layer arranged on the first titanium layer;
9 a second titanium layer arranged on the aluminum-based metal layer and
10 contacting the first electrode;

11 a first titanium nitride layer disposed between the first titanium layer and the
12 aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first
13 titanium layer and aluminum from the aluminum-based metal layer reacting with each other;
14 and

15 a second titanium nitride layer disposed between the second titanium layer and
16 the aluminum-based metal layer, the second titanium nitride layer preventing titanium from

17 the second titanium layer and aluminum from the aluminum-based metal layer reacting with
18 each other;

19 wherein the titanium nitride ~~layer contains~~ layers contain 5 to 85wt% of
20 nitrogen.

1 30. (Currently Amended) The flat panel display of claim 29, wherein the first
2 titanium nitride layer has a thickness of about 100 to 600Å.

1 31. (Previously Presented) The flat panel display of claim 29, wherein the first
2 titanium nitride layer has a thickness of about 100 to 400Å.

1 32. (Previously Presented) The flat panel display of claim 29, wherein the second
2 titanium nitride layer has a thickness of about 200 to 600Å.

1 33. (Currently Amended) The flat panel display of claim 29, wherein the second
2 titanium nitride ~~layers have~~ layer has a thickness of about 300Å.

1 34. (Previously Presented) A flat panel display, comprising a plurality of
2 sub-pixels driven by thin film transistors, each of the thin film transistors including a source
3 electrode, a drain electrode, a gate electrode, and a polysilicon semiconductor layer each of
4 the sub-pixels including a first electrode, a second electrode, and an emitting layer disposed

5 between the first electrode and the second electrode, wherein one of the source electrode and
6 the drain electrode includes:

7 a first titanium layer contacting the semiconductor layer;
8 an aluminum-based metal layer arranged on the first titanium layer;
9 a second titanium layer arranged on the aluminum-based metal layer and
10 contacting the first electrode;

11 a first titanium nitride layer disposed between the first titanium layer and the
12 aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first
13 titanium layer and aluminum from the aluminum-based metal layer reacting with each other;
14 and

15 a second titanium nitride layer disposed between the second titanium layer and
16 the aluminum-based metal layer, the second titanium nitride layer preventing titanium from
17 the second titanium layer and aluminum from the aluminum-based metal layer reacting with
18 each other;

19 wherein the aluminum-based metal layer is an aluminum alloy containing about
20 0.5 to 5 wt% of one element being selected from the group consisting of silicon, copper,
21 neodymium, platinum, and nickel.

1 35. (Previously Presented) The flat panel display of claim 34, wherein the
2 aluminum-based metal layer is an aluminum-silicon alloy containing about 2 wt% of silicon.